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. * PALM INTRANET

Day: Tuesday Date: 4/25/2006

Time: 11:18:13

Inventor Information for 10/705579

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WEBB, ERIC G.	SALEM	OREGON
SUKAMTO, JOHANES H.	LAKE OSWEGO	OREGON
Appln Info Contents Petition Info	Atty/Agent Info Continu	ity Data Foreign Data
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US	20050818	Methods of	438/654	438/627;	Kailasam,
20050181598	20030818	providing an	150/051	438/628;	Sridhar K.
A1		adhesion layer for		438/652;	
AI		adhesion of barrier		438/653;	
		and/or seed layers		438/677;	
		to dielectric films		438/687	
TIC	20050512	Methods for the	205/183	205/186;	Kailasam,
US	20030312	electrochemical	203/163	205/180;	Sridhar K. et al.
20050098440				205/291	Official 18. Of all
A1		deposition of copper onto a		203/271	
		barrier layer of a			
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	20041125	work piece	205/137	205/143	Webb, Eric G.
US	20041125	Electroplating using DC current	203/137	203/143	et al.
20040231996					ct al.
A1		interruption and			
		variable rotation	!	•	
710	00040715	rate	385/142	385/129	Drewery, John
US	20040715	Erbium-doped	383/142	363/129	S. et al.
20040136681		oxide glass			S. et al.
A1	2000000	T-1	156/245 42	119/702E	Drewery, John
US	20030130	Electrostatic control	156/345.43	118/723E;	Diewery, John
20030019582		of deposition of,	1	118/723I;	
A1		and etching by,		118/723R;	
		ionized materials in		118/728;	
		semiconductor		156/345.47;	
		processing		156/345.48;	
			1.56/2.45.42	156/345.51	Dunnami John
US	20030130	RF BIAS	156/345.43	118/723E;	Drewery, John
20030019581		CONTROL IN		118/723I;	
A1		PLASMA		118/723R;	
	1	DEPOSITION		156/345.44;	
		AND ETCH		156/345.47;	·
		SYSTEMS WITH		156/345.48	
		MULTIPLE RF			
		POWER			
		SOURCES		110/500 137	D 1 T 6-4
US	20021212	Inductively-coupled	156/345.48	118/723AN	Brcka, Jozef et
20020185229		plasma processing			al.
A1		system		70/000	1 1 1 T
US	20021017	Wooden floor truss	52/299	52/292	Webb, Eric
20020148182		and foundation wall			
A1		assembly			<u> </u>
US	20020808	Method and	204/192.1	204/192.12;	Drewery, John
20020104751		apparatus for		204/298.06;	Stephen et al.
A1		ionized physical		204/298.09;	
		vapor deposition		204/298.11;	<u> </u>

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				204/298.17;	
				204/298.18; 204/298.19	
US 20020074238 A1	20020620	Method and apparatus for uniform electropolishing of damascene ic structures by selective agitation	205/660	204/217; 204/224M; 204/241; 205/656; 205/662; 205/663; 205/672; 205/682; 205/684; 205/686; 257/E21.304; 257/E21.309	Mayer, Steven T. et al.
US 20020029538 A1	20020314	Steel floor truss	52/693	52/634; 52/690; 52/691	Webb, Eric
US 20020025449 A1	20020228	AN ELECTROACTIVE FILM ON A SUBSTRATE AND METHOD OF MAKING	428/689	205/106; 205/108; 205/198; 205/316; 205/334	SUKAMTO, JOHANES H. et al.
US 20020013186 A1	20020131	Break-away, low resistance golf tee	473/399		Webb, Eric
US 6974768 B1	20051213	Methods of providing an adhesion layer for adhesion of barrier and/or seed layers to dielectric films	438/625	438/627; 438/628; 438/629; 438/643; 438/644; 438/648; 438/653; 438/654; 438/656	Kailasam; Sridhar K.
US 6884335 B2	20050426	Electroplating using DC current interruption and variable rotation rate	205/104	205/143; 205/157; 205/261; 205/291; 428/687; 428/935	Webb; Eric G. et al.
US 6790773 B1	20040914	Process for forming barrier/seed structures for integrated circuits	438/643	438/644; 438/653; 438/654; 438/678;	Drewery; John S. et al.

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				438/688	
US 6774039	20040810	Process scheme for	438/687	257/E21.175;	Drewery; John
B1	20040810	improving	430/007	257/E21.582;	S.
ы	ļ	electroplating		438/627;	0.
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US 6764168	20040720	Sensor for detecting	347/61		Henner W. et al.
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¥10 (85 (008	20040620	characteristics	438/691	205/640;	Kelly; John et
US 6756307	20040629	Apparatus for	438/091	•	al.
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		semiconductor		205/654;	
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		integrated circuit		29/855;	
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		interposer		438/458;	
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		flexible dielectric		438/622	
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		conductive posts			
US 6719886	20040413	· · · · · · · · · · · · · · · · · · ·	204/298.18	204/298.03;	Drewery; John
B2	200.0.12	apparatus for		204/298.06;	Stephen et al.
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US 6709557	20040323	Sputter apparatus	204/298.13	204/298.12	Kallasalli,

B1		for producing multi- component metal alloy films and method for making the same			Sridhar K. et al.
US 6699396 B1	20040302	Methods for electroplating large copper interconnects	216/40	257/E21.175; 257/E21.577; 257/E21.579; 257/E21.586; 257/E21.587	Drewery; John Stephen
US 6664122 B1	20031216	Electroless copper deposition method for preparing copper seed layers	438/17	257/E21.174; 257/E21.584; 438/687; 977/890	Andryuschenko; Tatyana N. et al.
US 6652711 B2	20031125	Inductively-coupled plasma processing system	156/345.48	118/723AN	Brcka; Jozef et al.
US 6620736 B2	20030916	Electrostatic control of deposition of, and etching by, ionized materials in semiconductor processing	438/710	118/720; 118/728; 156/345.3; 156/345.51; 427/569; 438/714; 438/716	Drewery; John
US 6607982 B1	20030819	High magnesium content copper magnesium alloys as diffusion barriers	438/687	257/E21.169; 257/E21.584; 438/618; 438/627; 438/643; 438/652; 438/653	Powell; Ronald A. et al.
US 6589887 B1		Forming metal- derived layers by simultaneous deposition and evaporation of metal	438/765	257/E21.169; 257/E21.576; 257/E21.579; 257/E21.584; 257/E23.167; 438/627; 438/643; 438/653; 438/660; 438/679; 438/680; 438/775	et al.
US 6537421 B2	20030325	RF bias control in plasma deposition and etch systems	156/345.48	156/345.28	Drewery; John

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US 6525829 B1	20030225	Method and apparatus for in-situ measurement of thickness of copper oxide film using optical reflectivity	356/630	356/632	Powell; Ronald A. et al.
US 6525407 B1	20030225	Integrated circuit package	257/666	257/668; 257/741; 257/747; 257/758; 257/759; 257/760; 257/762; 257/E23.067	Drewery; John Stephen
US 6486859 B1	20021126	Color displays	345/72	345/690	Croll; Michael George et al.
US 6417626 B1	20020709	Immersed inductively coupled plasma source	315/111.51	118/715; 118/723I; 204/298.15; 204/671; 315/111.21	Brcka; Jozef et al.
US 6287435 B1	20010911	Method and apparatus for ionized physical vapor deposition	204/298.09	204/298.06; 204/298.07; 204/298.08; 204/298.12; 204/298.17; 204/298.18	Drewery; John Stephen et al.
US 6197165 B1	20010306	Method and apparatus for ionized physical vapor deposition	204/192.12	204/298.08; 204/298.11; 204/298.12; 204/298.16; 204/298.19; 204/298.26	Drewery; John S. et al.
US 6080287 A	20000627	Method and apparatus for ionized physical vapor deposition	204/192.15	204/192.12; 204/298.06; 204/298.08; 204/298.11; 204/298.15; 204/298.16; 204/298.21	Drewery; John S. et al.
US 5956091 A	19990921	Method of showing 16:9 pictures on 4:3 displays	348/445	348/580	Drewery; John Oliver et al.

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US 5426465 A	19950620	Television systems	348/427.1	348/392.1	Drewery; John O.
US 5333014 A	19940726	Non-sharp cut filters for assembling and splitting in Weston Clean PAL	348/453	348/471; 348/493; 348/624; 348/663	Drewery; John O. et al.
US 4897716 A	19900130	Method and apparatus for adaptively displaying video signals	348/452	348/474	Drewery; John O. et al.
US 4843468 A	19890627	Scanning techniques using hierarchical set of curves	348/441	345/25; 345/428; 348/325; 365/23	Drewery; John O.
US 4322750 A	19820330	Television display system	348/447	345/643; 348/910	Lord; Arthur V. et al.
US 4322739 A	19820330	Processing of N.T.S.C. color television signals	348/392.1		Drewery; John O. et al.
US 4296434 A	19811020	Method of and apparatus for movement portrayal with a raster e.g. television, display	348/579	348/582	Drewery; John O. et al.
US 4288810 A	19810908	Method of and apparatus for deriving a PAL color television signal corresponding to any desired field in an 8-field PAL sequence from one stored field or picture of a PAL signal	348/662	348/453; 348/654	Drewery; John O. et al.
US 4249210 A	19810203	Video noise reduction system	348/620		Storey; Richard et al.
US 4223341 A	19800916	Circuitry providing a delayed color television signal having luminance and chrominance components derived	348/662		Drewery; John O.

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US 4212028	19800708	Processing pal color	375/240.01		Drewery; John
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